1 A very low V_F MEGA Schottky barrier rectifiers

Rev. 02 — 22 March 2007

Pro

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small and flat lead Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	
PMEG4010CEH	SOD123F	-	single
PMEG4010CEJ	SOD323F	SC-90	single

1.2 Features

Forward current: I_F ≤ 1 A

Reverse voltage: V_R ≤ 40 V

Very low forward voltage

Small and flat lead SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	1	Α
V_R	reverse voltage		-	-	40	V
V_{F}	forward voltage	I _F = 1 A	<u>[1]</u> _	490	570	mV

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



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Pinning information

Table 3. **Pinning**

Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	1 1 2 sym001

^[1] The marking bar indicates the cathode.

Ordering information

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
PMEG4010CEH	·-	plastic surface-mounted package; 2 leads	SOD123F
PMEG4010CEJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

Marking

Table 5. **Marking codes**

3	
Type number	Marking code
PMEG4010CEH	C9
PMEG4010CEJ	EP

Product data sheet

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	40	V
l _F	forward current	T _{sp} ≤ 55 °C	-	1	Α
I _{FRM}	repetitive peak forward current	$\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$	-	7	Α
I _{FSM}	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$			
	PMEG4010CEH		-	9	Α
	PMEG4010CEJ		-	10	Α
P_{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PMEG4010CEH		<u>[1]</u> -	375	mW
			[2] -	830	mW
	PMEG4010CEJ		<u>[1]</u> -	350	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	тур Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	PMEG4010CEH		[2] _	-	330	K/W
			[3] _	-	150	K/W
	PMEG4010CEJ		[2] _	-	350	K/W
			[3] _	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[4]</u>			
	PMEG4010CEH		-	-	60	K/W
	PMEG4010CEJ		-	-	55	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[4] Soldering point of cathode tab.

7. Characteristics

Table 8. **Characteristics**

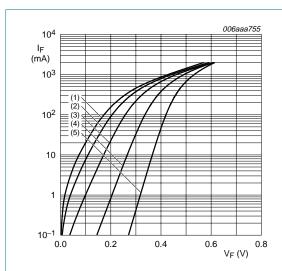
 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

· and – 20	e ameee care, mee					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage	forward voltage		<u>[1]</u>			
	$I_F = 1 \text{ mA}$	-	210	240	mV	
		I _F = 10 mA	-	270	310	mV
		I _F = 100 mA	-	340	390	mV
		$I_F = 500 \text{ mA}$	-	420	490	mV
		I _F = 700 mA	-	450	520	mV
		I _F = 1 A	-	490	570	mV
I _R	reverse current	V _R = 5 V	-	0.8	-	μΑ
	V _R = 10 V	-	1.1	-	μΑ	
		V _R = 40 V	-	6	50	μΑ
C _d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	69	77	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

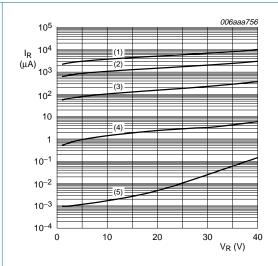
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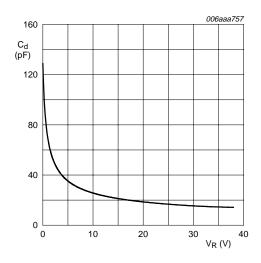
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \,^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

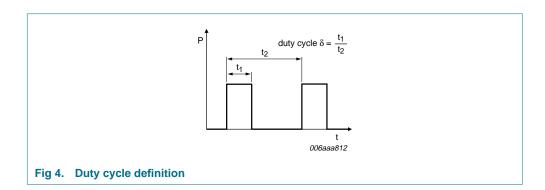


f = 1 MHz; T_{amb} = 25 °C

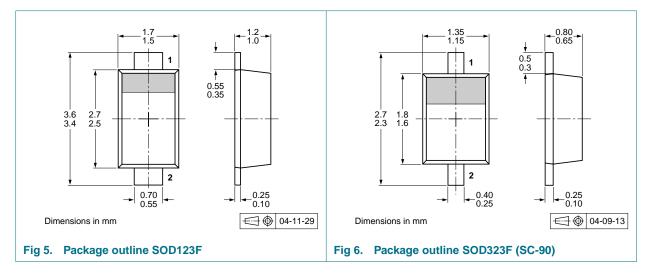
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Test information



9. Package outline



10. Packing information

Table 9. Packing methods

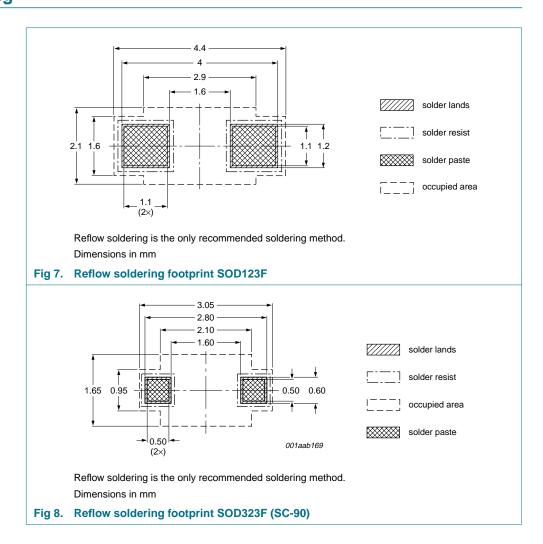
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG4010CEH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG4010CEJ	SOD323F			

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4010CEH_PMEG4010CEJ_2	20070322	Product data sheet	-	PMEG4010CEJ_1
Modifications:	 The format identity guid 	ly with the new		
	 Legal texts 	have been adapted to the ne	ew company name v	vhere appropriate.
	 Type number 	er PMEG4010CEH added		
	Section 1.1	"General description": amer	nded	
	• Table 1 "Pro	oduct overview": added		
	• Table 7 "The	ermal characteristics": Table	note 1 amended	
	 Section 8 "7 	est information": added		
PMEG4010CEJ_1	20060413	Product data sheet	-	-

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Product data sheet

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMEG4010CEH; PMEG4010CEJ

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